



# SPP3481

## P-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPP3481 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

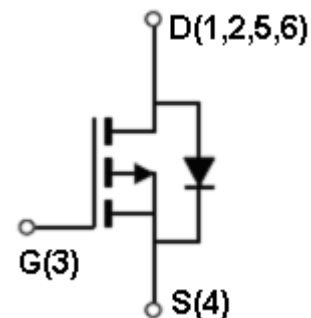
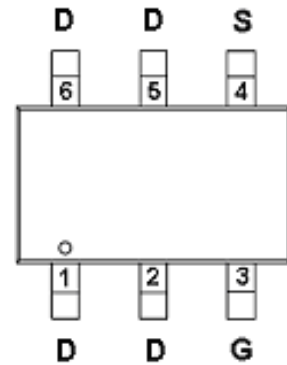
### FEATURES

- ◆ -30V/-5.2A, $R_{DS(ON)}=55m\Omega@V_{GS}=-10V$
- ◆ -30V/-4.2A, $R_{DS(ON)}=75m\Omega@V_{GS}=-4.5V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TSOP-6P package design

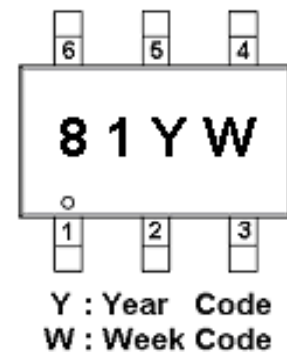
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION(TSOP-6P)



### PART MARKING





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### PIN DESCRIPTION

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPP3481ST6RG	TSOP-6P	81YW
SPP3481ST6RGB	TSOP-6P	81YW

- ※ Week Code : A ~ Z ( 1 ~ 26 ) ; a ~ z ( 27 ~ 52 )
- ※ SPP3481ST6RG : Tape Reel ; Pb – Free
- ※ SPP3481ST6RGB : Tape Reel ; Pb – Free; Halogen – Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	-30	V	
Gate –Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	TA=25°C	-5.2	A
		TA=70°C	-4.2	
Pulsed Drain Current	I <sub>DM</sub>	-20	A	
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-1.7	A	
Power Dissipation	P <sub>D</sub>	TA=25°C	2.0	W
		TA=70°C	1.3	
Operating Junction Temperature	T <sub>J</sub>	150	°C	
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C	
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	90	°C/W	



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### ELECTRICAL CHARACTERISTICS

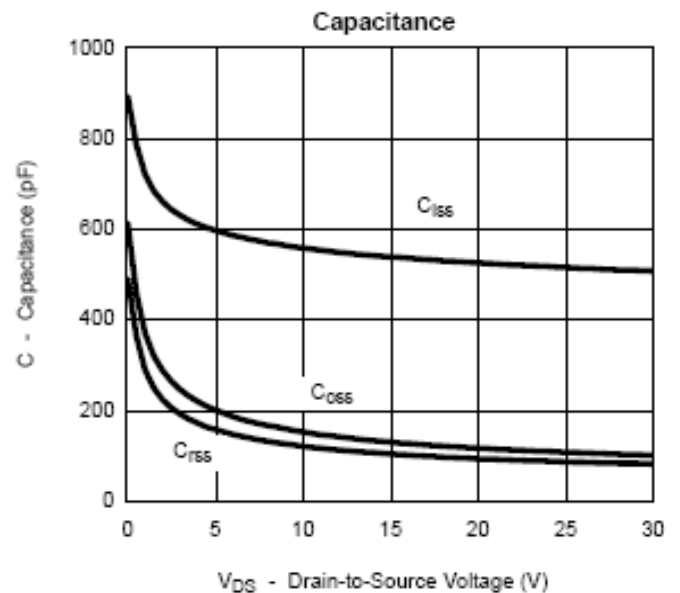
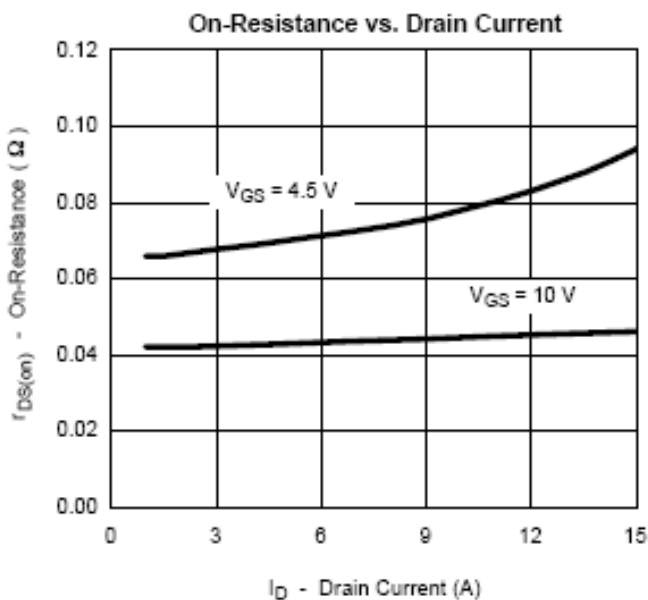
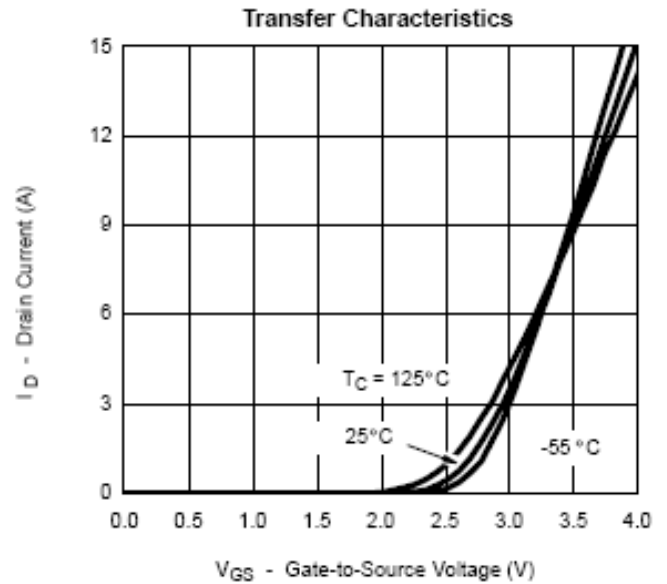
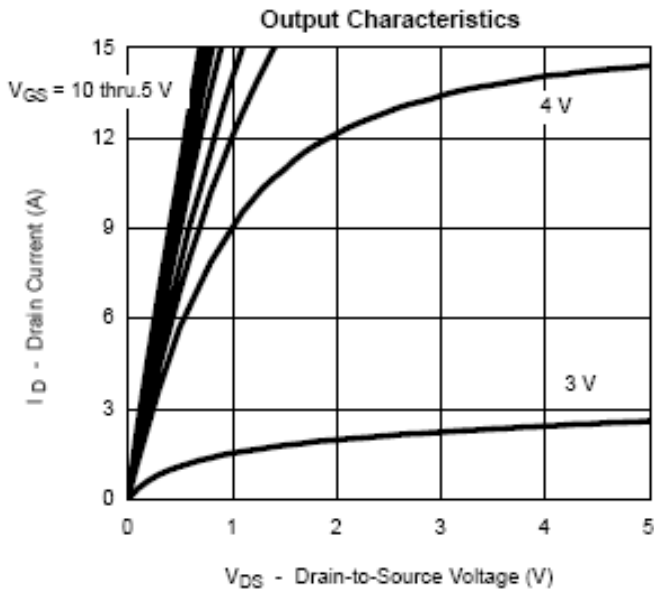
( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0		-3.0	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-21V, V_{GS}=0V$			-2	uA
		$V_{DS}=-21V, V_{GS}=0V$ $T_J=55^{\circ}\text{C}$			-10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-10V$	-10			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-5.2A$		0.042	0.055	$\Omega$
		$V_{GS}=-4.5V, I_D=-4.2A$		0.058	0.075	
Forward Transconductance	$g_{fs}$	$V_{DS}=-5.0V, I_D=-4.0A$		10		S
Diode Forward Voltage	$V_{SD}$	$I_S=-1.0A, V_{GS}=0V$		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-15V, V_{GS}=-10V$ $I_D=-4.0A$		14	21	nC
Gate-Source Charge	$Q_{gs}$			1.9		
Gate-Drain Charge	$Q_{gd}$			3.7		
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V$ $f=1\text{MHz}$		540		pF
Output Capacitance	$C_{oss}$			131		
Reverse Transfer Capacitance	$C_{rss}$			105		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=15\Omega$ $I_D=-1.0A, V_{GEN}=-10V$ $R_G=6\Omega$		10	15	ns
	$t_r$			15	25	
Turn-Off Time	$t_{d(off)}$			31	50	
	$t_f$			20	30	



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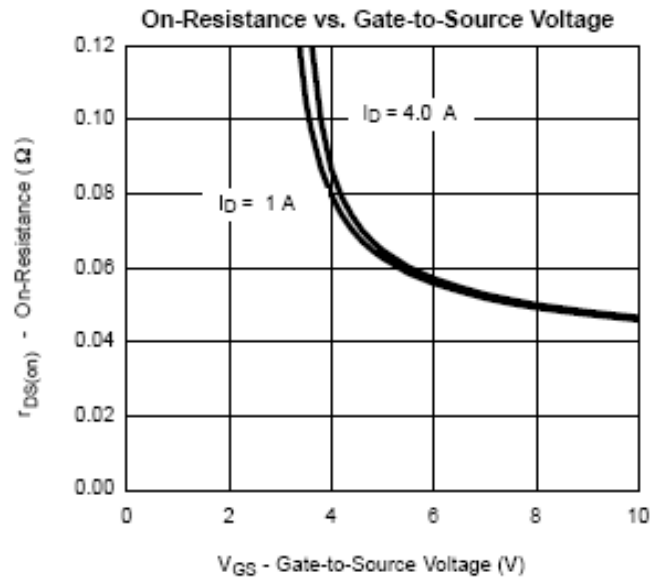
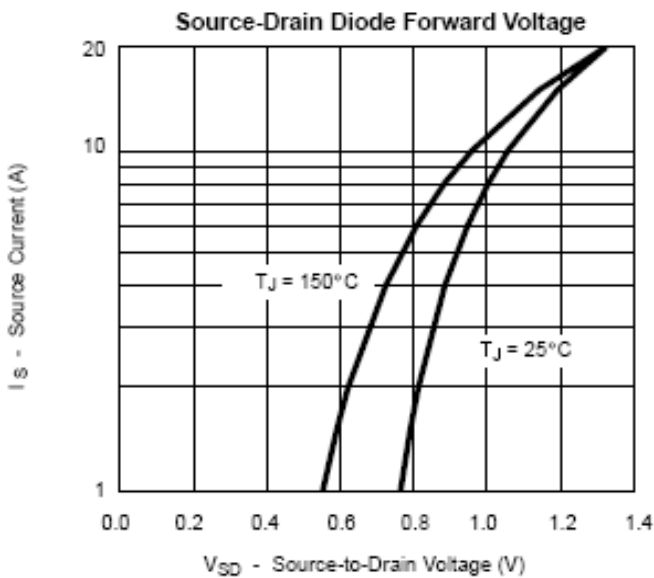
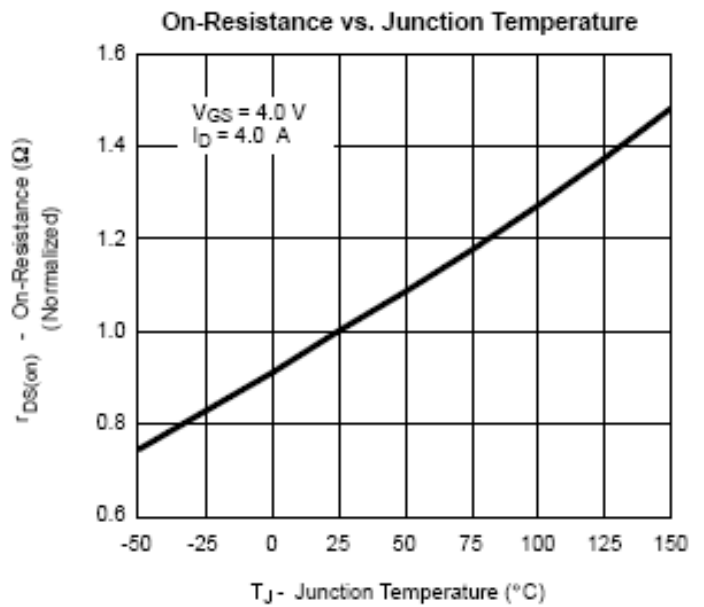
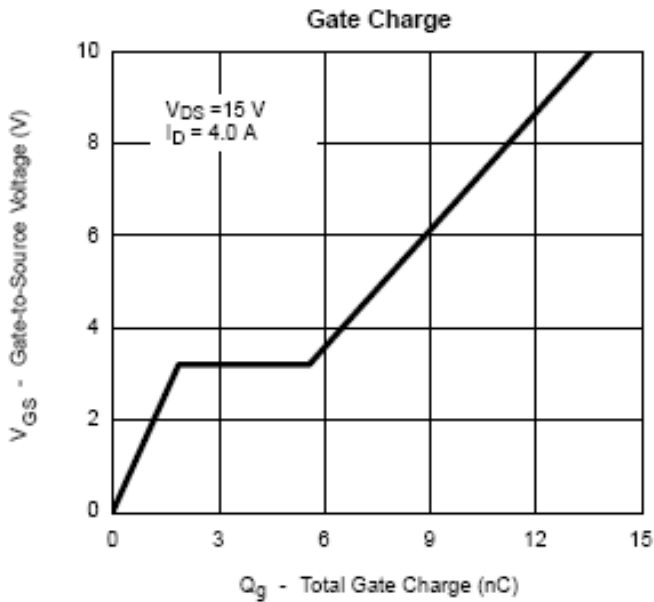
## TYPICAL CHARACTERISTICS





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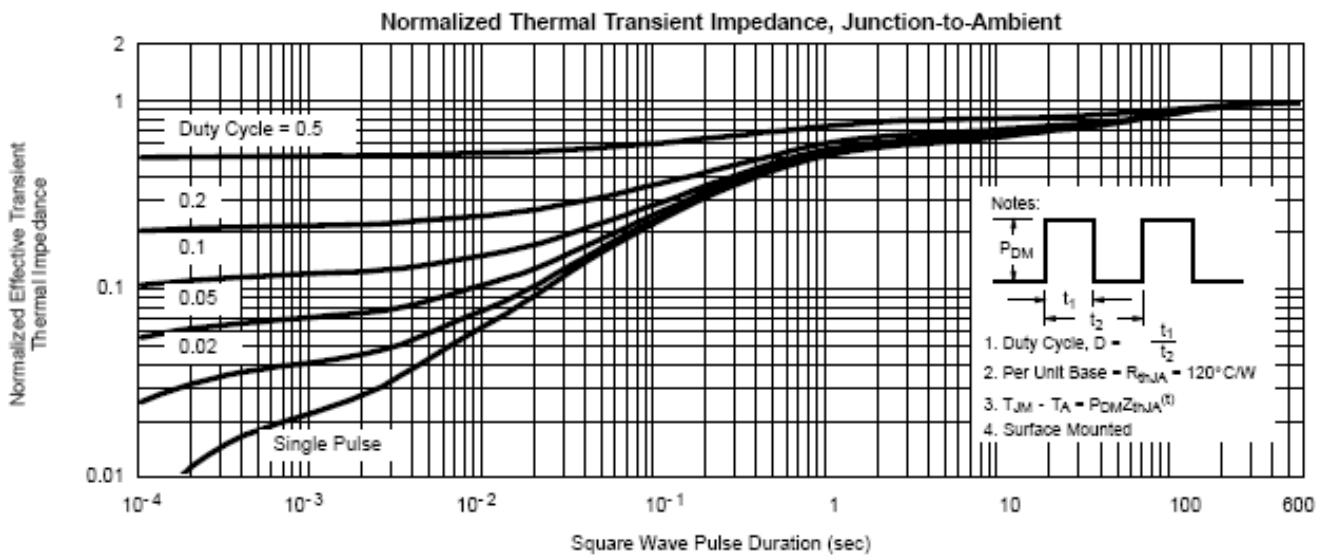
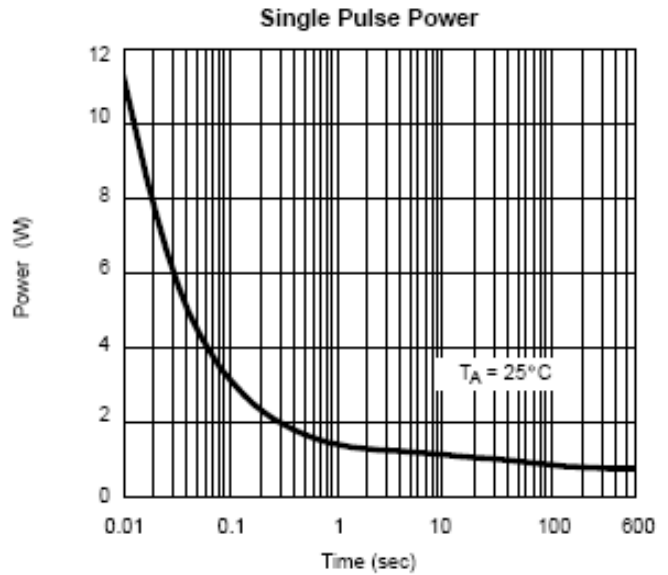
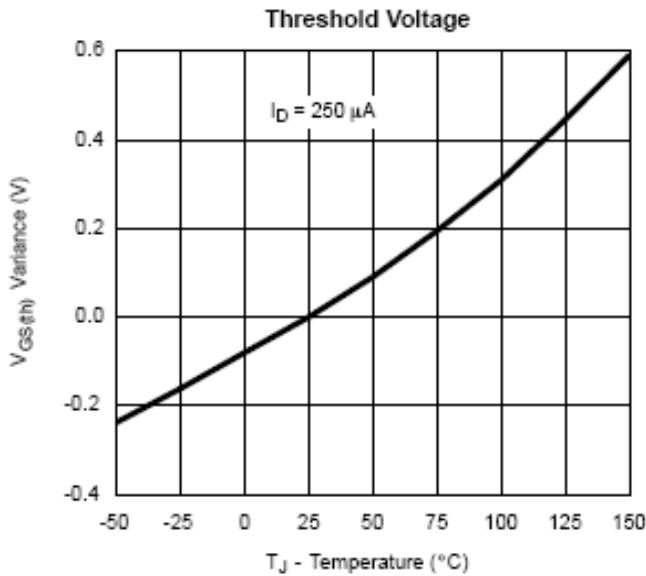
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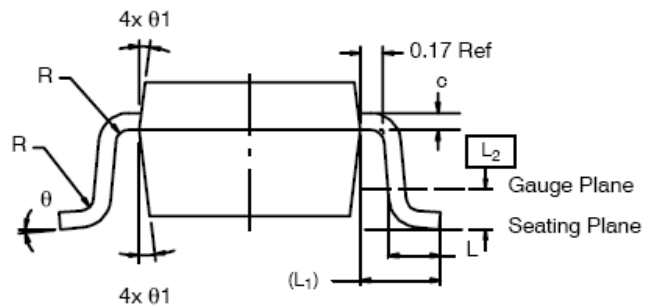
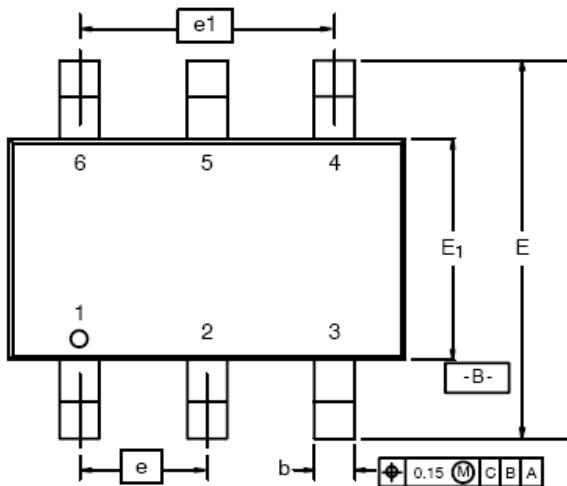




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### TSOP- 6P PACKAGE OUTLINE



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
<b>A</b>	0.91	-	1.10	0.036	-	0.043
<b>A<sub>1</sub></b>	0.01	-	0.10	0.0004	-	0.004
<b>A<sub>2</sub></b>	0.90	-	1.00	0.035	0.038	0.039
<b>b</b>	0.30	0.32	0.45	0.012	0.013	0.018
<b>c</b>	0.10	0.15	0.20	0.004	0.006	0.008
<b>D</b>	2.95	3.05	3.10	0.116	0.120	0.122
<b>E</b>	2.70	2.65	2.98	0.106	0.112	0.117
<b>E<sub>1</sub></b>	1.55	1.65	1.70	0.061	0.065	0.067
<b>e</b>	1.00 BSC			0.0394 BSC		
<b>e<sub>1</sub></b>	1.90	2.00	2.10	0.075	0.080	0.085
<b>L</b>	0.35	-	0.50	0.014	-	0.020
<b>L<sub>1</sub></b>	0.60 Ref			0.024 Ref		
<b>L<sub>2</sub></b>	0.25 BSC			0.010 BSC		
<b>R</b>	0.10	-	-	0.004	-	-
<b>θ</b>	0°	4°	8°	0°	4°	8°
<b>θ<sub>1</sub></b>	7° Nom			7° Nom		



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